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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



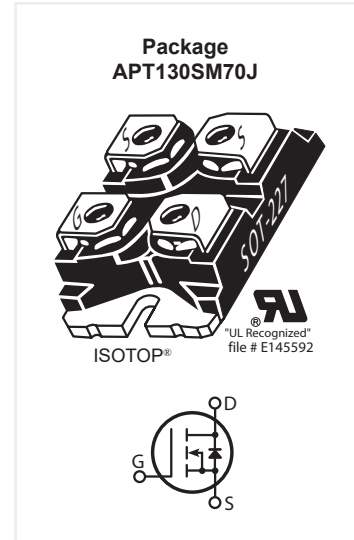
# APT130SM70J

700V, 78A, 35mΩ

## Silicon Carbide N-Channel Power MOSFET

### DESCRIPTION

Silicon carbide (SiC) power MOSFET product line from Microsemi increase your performance over silicon MOSFET and silicon IGBT solutions while lowering your total cost of ownership for high-voltage applications.



### FEATURES / TYPICAL APPLICATIONS

**SiC MOSFET Features:**

- Low on-resistance virtually independent on the ambient temperature
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature,  $T_j(\text{max}) = +175\text{C}$
- Fast and reliable body diode
- Superior avalanche ruggedness

**SiC MOSFET Benefits:**

- High efficiency to enable lighter/compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need of external Free Wheeling Diode
- Lower system cost of ownership

**Applications:**

- PV inverter, converter and industrial motor drives
- Smart grid transmission & distribution
- Induction heating, and welding
- H/EV powertrain and EV charger
- Power supply and distribution

### MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain Source Voltage	700	V
$I_D$	Continuous Drain Current @ $T_c = 25^\circ\text{C}$	78	A
	Continuous Drain Current @ $T_c = 100^\circ\text{C}$	55	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	270	
$V_{GS}$	Gate-Source Voltage	-10 to +25	V
$P_D$	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	273	W
	Linear Derating Factor	1.82	W/°C

### THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance		0.34	0.55	°C/W
$T_j$	Operating Junction Temperature	-55		175	°C
$T_{stg}$	Storage Junction Temperature Range	-55		150	
$W_T$	Package Weight			1.03	oz
Torque	Mounting Torque (SOT-227 Package), 6-32 or M3 screw		5	10	in·lbf
			.56	1.13	N·m

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## STATIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	700			V
$R_{DS(on)}$	Drain-Source On Resistance <sup>②</sup>	$V_{GS} = 20V, I_D = 60A$		35	45	mΩ
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1mA$	1.7	2.4		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient			-5.1		mV/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 700V$ $V_{GS} = 0V$		$T_J = 25^\circ C$	100	μA
				$T_J = 150^\circ C$	250	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS} = +20V / -10V$			±100	nA
ESR	Equivalent Series Resistance	$f = 1MHz, 25mV, \text{Drain Short}$		0.46		Ω

$T_J = 25^\circ C$  unless otherwise specified

## DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V, V_{DD} = 700V$ $f = 1MHz$		3950		pF
$C_{rss}$	Reverse Transfer Capacitance			50		
$C_{oss}$	Output Capacitance			465		
$Q_g$	Total Gate Charge	$V_{GS} = 0/20V$		270		nC
$Q_{gs}$	Gate-Source Charge	$V_{DD} = 466V$		42		
$Q_{gd}$	Gate-Drain Charge	$I_D = 60A$		61		
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 466V$ $V_{GS} = 0/20V$ $I_D = 60A$ $R_G = 1.5 \Omega$ <sup>③</sup> $L = 115 \mu H$ $T_c = 25^\circ C$ Freewheeling Diode = APT20SCE65B		17		ns
$t_r$	Current Rise Time			15		
$t_{d(off)}$	Turn-Off Delay Time			36		
$t_f$	Current Fall Time			19		
$E_{on2}$	Turn-On Switching Energy <sup>④</sup>	$V_{DD} = 466V$ $V_{GS} = 0/20V$ $I_D = 60A$ $R_G = 1.5 \Omega$ <sup>③</sup> $L = 115 \mu H$ $T_c = 150^\circ C$ Freewheeling Diode = APT20SCE65B		1060		μJ
$E_{off}$	Turn-Off Switching Energy			305		
$t_{d(on)}$	Turn-On Delay Time			16		ns
$t_r$	Current Rise Time			15		
$t_{d(off)}$	Turn-Off Delay Time			39		
$t_f$	Current Fall Time			21		
$E_{on2}$	Turn-On Switching Energy <sup>④</sup>			965		μJ
$E_{off}$	Turn-Off Switching Energy			345		

### Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{SD}$	Diode Forward Voltage	$I_{SD} = 60A, V_{GS} = 0V$		3.85		V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 60A, V_{DD} = 466V$ $di/dt = -1000A/\mu s$		68		ns
$Q_{rr}$	Reverse Recovery Charge			460		nC
$I_{rrm}$	Reverse Recovery Current			15		A

$T_J = 25^\circ C$  unless otherwise specified

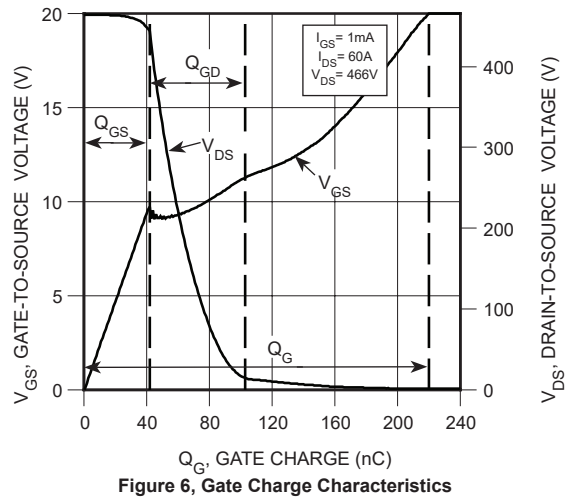
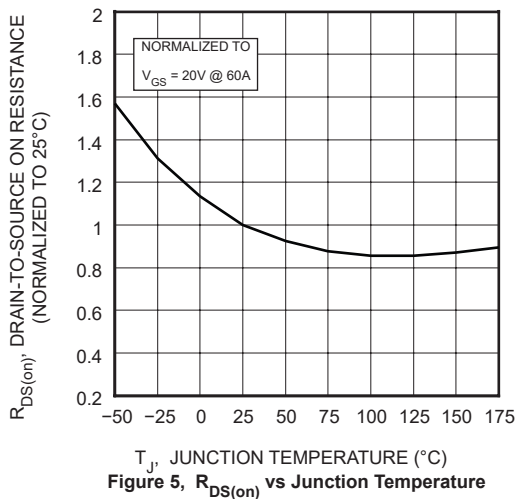
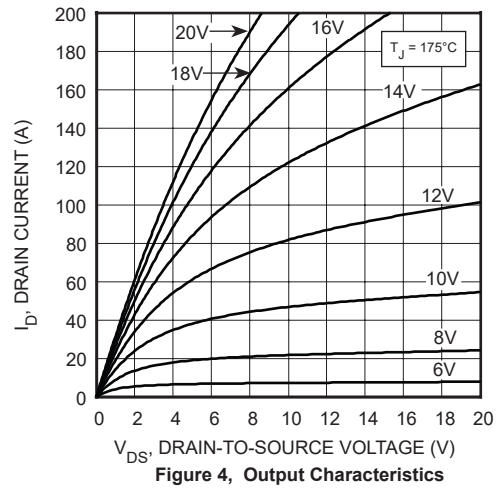
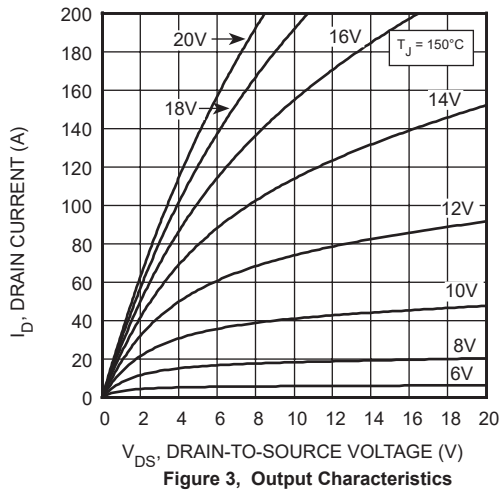
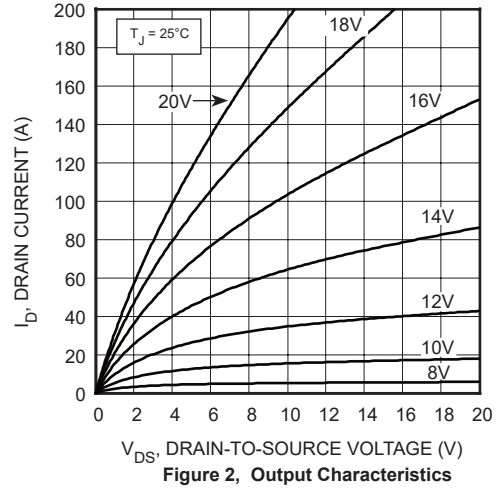
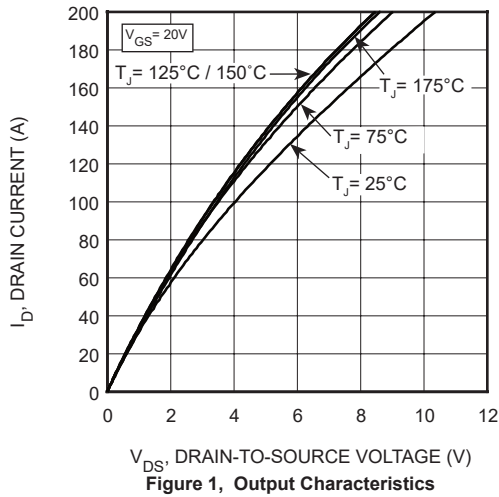
① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature

② Pulse test: Pulse Width < 380μs, duty cycle < 2%.

③  $R_G$  is total gate resistance including internal gate driver impedance.

④  $E_{on2}$  includes energy of APT20SCE65B free wheeling diode.

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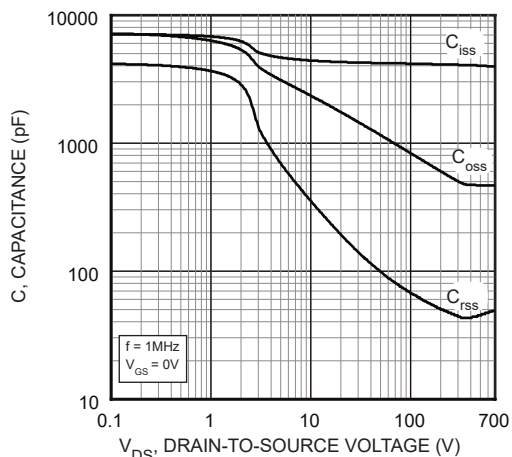


Figure 7, Capacitance vs Drain-to-Source Voltage

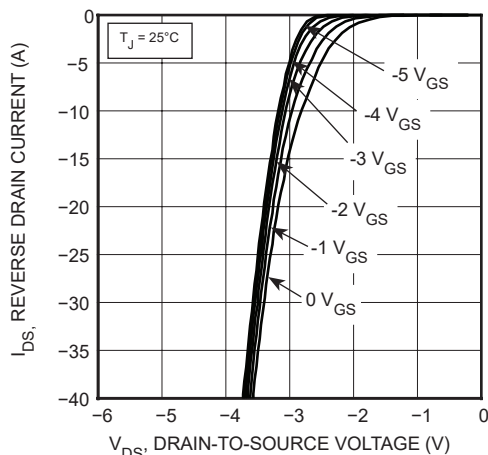


Figure 8, Reverse Drain Current vs Drain-to-Source Voltage  
Third Quadrant Conduction

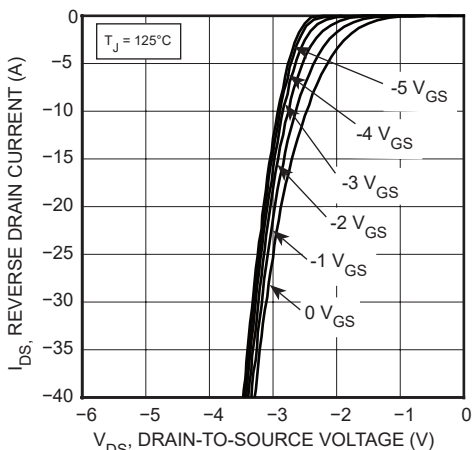


Figure 9, Reverse Drain Current vs Drain-to-Source Voltage  
Third Quadrant Conduction

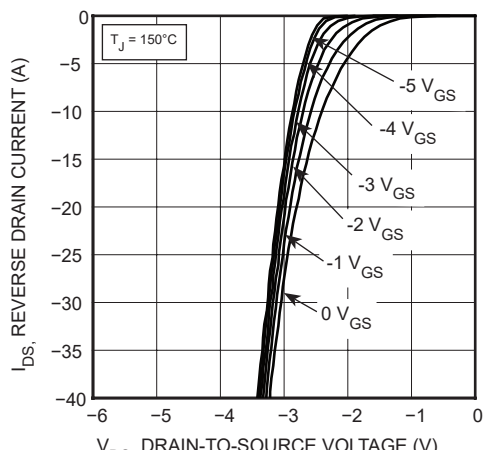


Figure 10, Reverse Drain Current vs Drain-to-Source Voltage  
Third Quadrant Conduction

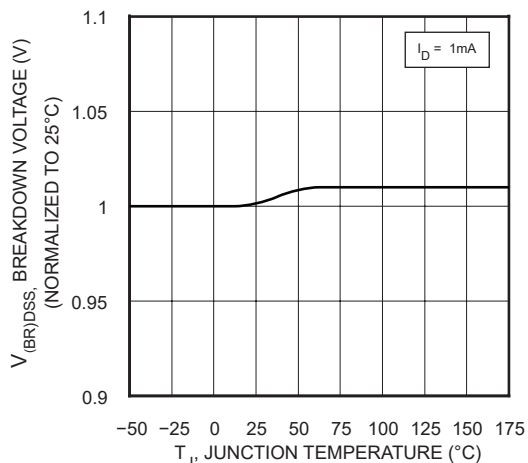


Figure 11, Breakdown Voltage vs Temperature

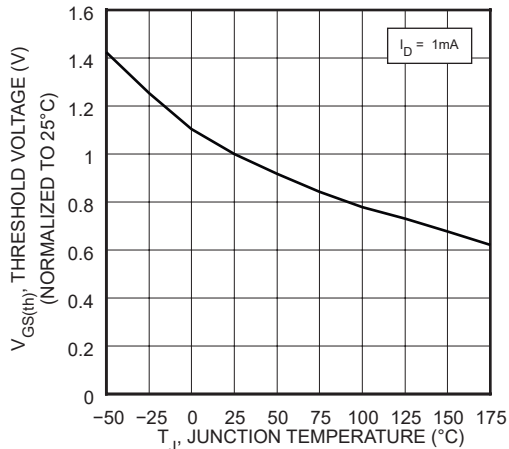


Figure 12, Threshold Voltage vs Temperature

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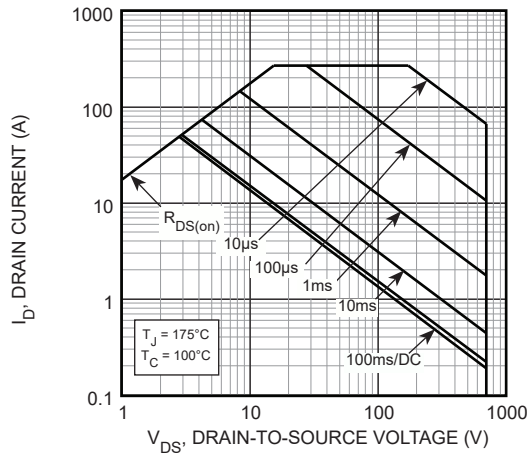


Figure 13, Forward Safe Operating Area

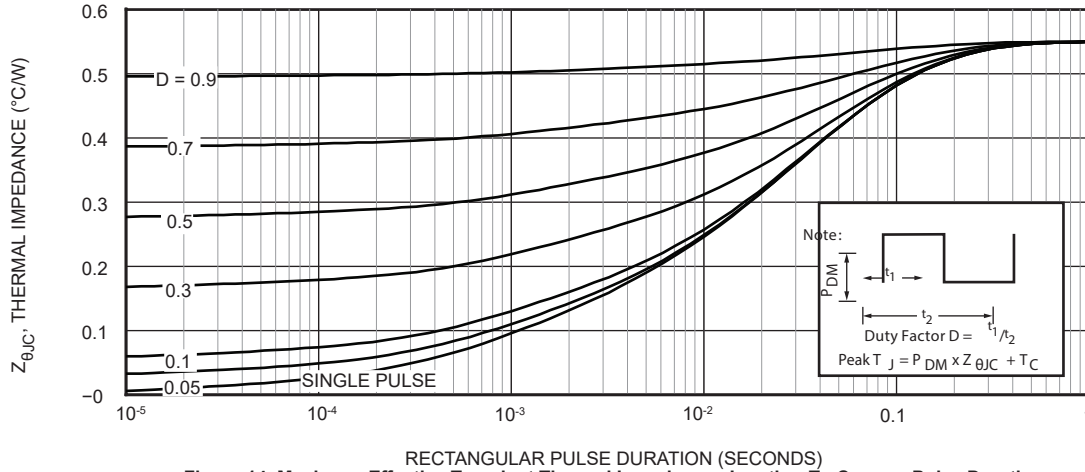
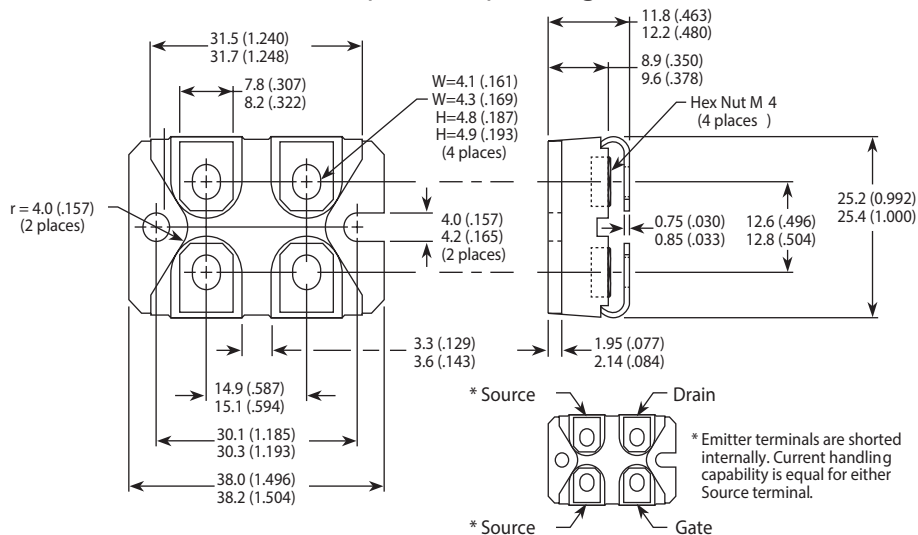


Figure 14, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

## SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters (Inches)

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Microsemi Corporate Headquarters  
One Enterprise, Aliso Viejo, CA 92656 USA  
Within the USA: +1 (800) 713-4113  
Outside the USA: +1 (949) 380-6100  
Sales: +1 (949) 380-6136  
Fax: +1 (949) 215-4996  
email: [sales.support@microsemi.com](mailto:sales.support@microsemi.com)  
[www.microsemi.com](http://www.microsemi.com)

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